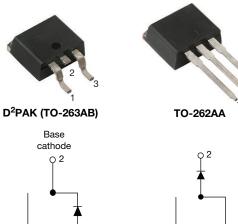
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VS-8ETH06SHM3, VS-8ETH06-1HM3

Vishay Semiconductors

Hyperfast Rectifier, 8 A FRED Pt[®]



0 1 0 3 N/C Anode

VS-8ETH06SHM3

VS-8ETH06-1HM3

- 3

Anode

서 1

N/C

2

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS									
I _{F(AV)}	8 A								
V _R	600 V								
V _F at I _F	1.3 V								
t _{rr} typ.	18 ns								
T _J max.	175 °C								
Package	D ² PAK (TO-263AB), TO-262AA								
Circuit configuration	Single								

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



FREE

- AEC-Q101 qualified, meets JESD 201, class 1 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: D²PAK (TO-263AB), TO-262AA

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS						
Peak repetitive reverse voltage	V _{RRM}		600	V						
Average rectified forward current	I _{F(AV)}	T _C = 144 °C	8							
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	90	А						
Peak repetitive forward current	I _{FM}		16							
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C						

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)											
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS					
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-	V					
Forward voltage	V _F	I _F = 8 A	-	2.0	2.4	v					
Forward voltage		I _F = 8 A, T _J = 150 °C	-	1.3	1.8						
Deverse leekerse eurrent		$V_{R} = V_{R}$ rated	-	0.03	50	μA					
Reverse leakage current	I _R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	- 55 500								
Junction capacitance	CT	V _R = 600 V	-	17	-	pF					
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH					

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1

Document Number: 96045

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DYNAMIC RECOVERY CHARACTERISTICS ($T_C = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST C	ONDITIONS	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time		$I_F = 1 \text{ A}, dI_F/dt = 100$) Α/μs, V _R = 30 V	-	18	22				
	+	$I_F = 8 \text{ A}, dI_F/dt = 100$) A/µs, V _R = 30 V	-	20	-	ns			
	t _{rr}	T _J = 25 °C		-	25	-	115			
		T _J = 125 °C		-	40	-				
De als vera avera avera at	1	T _J = 25 °C	I _F = 8 A dI _F /dt = 200 A/μs	-	2.4	-	A			
Peak recovery current	I _{RRM}	T _J = 125 °C	$V_{\rm B} = 390 \rm V$	-	4.8	-				
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	25	-	nC			
neverse recovery charge	Qrr	T _J = 125 °C		-	120	-				
Reverse recovery time	t _{rr}		I _F = 8 A	-	33	-	ns			
Peak recovery current	I _{RRM}	T _J = 125 °C	dI _F /dt = 600 A/µs	-	12	-	Α			
Reverse recovery charge	Q _{rr}		V _R = 390 V	-	220	-	nC			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C				
Thermal resistance, junction to case per leg	R _{thJC}		-	1.4	2					
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-					
Weight			-	2.0	-	g				
weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking davias		Case style D ² PAK (TO-263AB)	8ETH06SH							
Marking device		Case style TO-262AA	8ETH06-1H							

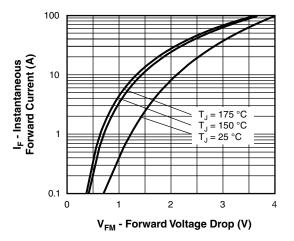


Fig. 1 - Maximum Forward Voltage Drop Characteristics

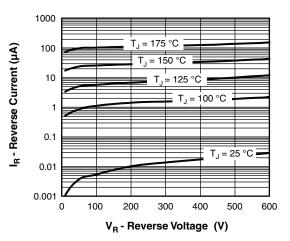


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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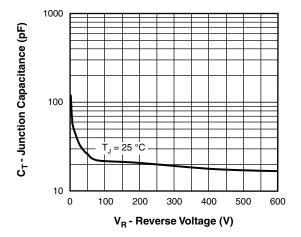


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

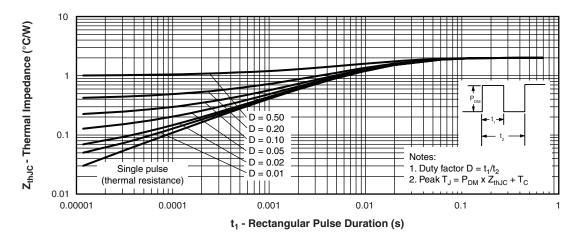
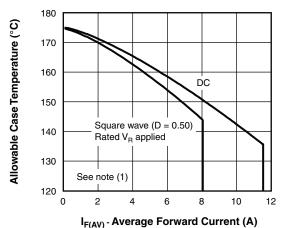
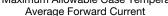


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics



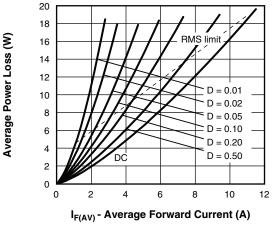




Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mbox{Pd} = \mbox{forward power loss} = \mbox{I}_{F(AV)} \times \mbox{V}_{FM} \mbox{ at } (\mbox{I}_{F(AV)}/\mbox{D}) \mbox{ (see fig. 6);} \\ \mbox{Pd}_{REV} = \mbox{inverse power loss} = \mbox{V}_{R1} \times \mbox{I}_{R} \mbox{ (1 - D); } \mbox{I}_{R} \mbox{ at } \mbox{V}_{R1} = \mbox{rated } \mbox{V}_{R} \end{array}$





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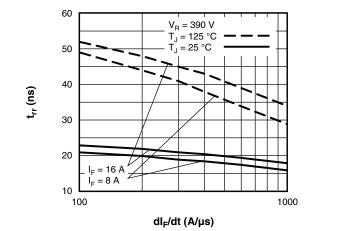


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

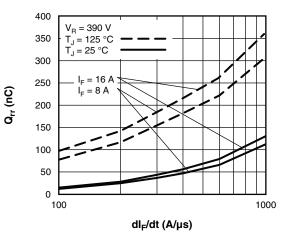
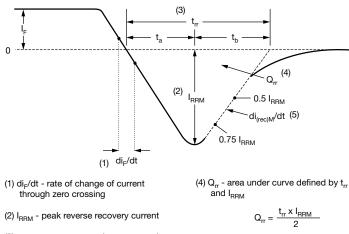


Fig. 8 - Typical Stored Charge vs. dl_F/dt



(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.



(5) $di_{(rec)M}/dt$ - peak rate of change of

current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions



Vishay Semiconductors

ORDERING INFORMATION TABLE

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VISHAY

Device code VS-	8	E	т	н	06	S	TRL	Н	М3
	2	3	4	5	6	7	8	9	10
П	- Vis	hav Sen	nicondu	ctors pro	oduct				
2	 Vishay Semiconductors product Current rating (8 A) 								
3									
4									
5	- H=	hyperfa	st rectif	ier					
6	- Vol	tage rati	ng (06 =	= 600 V)	1				
7	- •S	= D ² PA	К (ТО-2	63AB)					
	• -1	= TO-2	62						
8	8 - • None = tube (50 pieces)								
	 TRL = tape and reel (left oriented, for D²PAK package) 								
	 TRR = tape and reel (right oriented, for D²PAK package) 								
9	- H=	AEC-Q	101 qua	lufied					
10	- M3	= halog	en-free,	RoHS-	complia	nt, and	terminat	tions lea	ad (Pb)-

ORDERING INFORMATION (Example)									
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION							
VS-8ETH06SHM3	50	Antistatic plastic tube							
VS-8ETH06STRRHM3	800	13"diameter reel							
VS-8ETH06STRLHM3	800	13"diameter plastic reel							
VS-8ETH06-1HM3	50	Antistatic plastic tube							

LINKS TO RELATED DOCUMENTS									
Dimensions	D ² PAK (TO-263AB)	www.vishay.com/doc?95046							
Differisions	TO-262AA	www.vishay.com/doc?95419							
Part marking information	D ² PAK (TO-263AB)	www.vishay.com/doc?95444							
Fart marking information	TO-262AA	www.vishay.com/doc?95443							
Packaging information	D ² PAK (TO-263AB)	www.vishay.com/doc?95032							

Outline Dimensions



D²PAK

DIMENSIONS in millimeters and inches

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SHA



SYMBOL	MILLIMETERS		INC	HES	NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 08-Jul-15

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Outline Dimensions



Vishay Semiconductors

TO-262

DIMENSIONS in millimeters and inches



Lead tip -



E1 Plating



Е

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. А 4.06 4.83 0.160 0.190 2.03 A1 3.02 0.080 0.119 b 0.51 0.99 0.020 0.039 b1 0.51 0.89 0.020 0.035 4 b2 1.14 1.78 0.045 0.070 1.14 1.73 0.045 0.068 4 b3 0.38 0.74 0.015 0.029 С 0.38 0.58 0.015 0.023 4 c1 1.14 1.65 0.045 0.065 c2 D 8.51 9.65 0.335 0.380 2 D1 6.86 8.00 0.270 0.315 3 Е 9.65 10.67 0.380 0.420 2, 3 E1 7.90 8.80 0.311 0.346 3 0.100 BSC 2.54 BSC е L 13.46 14.10 0.530 0.555 L1 _ 1.65 0.065 3 _ 3.36 0.132 0.146 L2 3.71

3. - Anode

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Controlling dimension: inches

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

Outline conform to JEDEC TO-262 except A1 (maximum), (6) b (minimum), D1 (minimum) and L2 where dimensions derived the actual package outline

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